



## BD435

Preliminary

*NPN EPITAXIAL SILICON TRANSISTOR*

### NPN EPITAXIAL SILICON TRANSISTOR

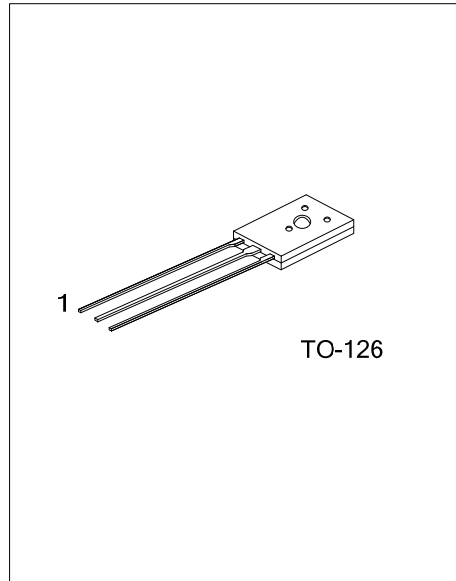
#### DESCRIPTION

The UTC **BD435** is a NPN epitaxial silicon transistor, it uses UTC's advanced technology to provide the customers with high DC current gain, etc.

The UTC **BD435** is suitable for medium power linear and switching applications.

#### FEATURES

\* High DC current gain



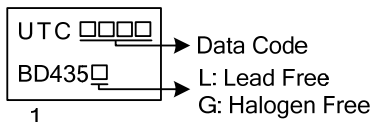
#### ORDERING INFORMATION

Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
BD435L-T60-K	BD435G-T60-K	TO-126	K	A	G	Bulk
BD435L-T60-K	BD435G-T60-K	TO-126	K	A	G	Bulk

Note: Pin assignment: G: Gate K: Cathode A: Anode

<p>BD435L-T60-K</p> <p>(1) Packing Type (2) Package Type (3) Green Package</p>	<p>(1) K: Bulk (2) T60: TO-126 (3) L: Lead Free, G: Halogen Free and Lead Free</p>
--	--

#### MARKING



■ ABSOLUTE MAXIMUM RATINGS ( $T_C=25^\circ\text{C}$ , unless otherwise noted)

PARAMETER	SYMBOL	RATINGS	UNIT
Collector-Base Voltage	$V_{CBO}$	32	V
Collector-Emitter Voltage	$V_{CEO}$	32	V
Collector-Emitter Voltage	$V_{CES}$	32	V
Emitter-Base Voltage	$V_{EBO}$	5	V
Collector Current (DC)	$I_C$	4	A
Collector Current (Pulse) (Note 1)	$I_{CP}$	7	A
Base Current	$I_B$	1	A
Collector Dissipation ( $T_C=25^\circ\text{C}$ )	$P_C$	36	W
Junction Temperature	$T_J$	150	$^\circ\text{C}$
Storage Temperature	$T_{STG}$	-65 ~150	$^\circ\text{C}$

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

■ ELECTRICAL CHARACTERISTICS ( $T_C=25^\circ\text{C}$ , unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Collector-Emitter Sustaining Voltage	$V_{CEO(SUS)}$	$I_C=100\text{mA}$ , $I_B=0\text{A}$	32			V
Collector Cut-Off Current	$I_{CBO}$	$V_{CB}=32\text{V}$ , $I_E=0$			100	$\mu\text{A}$
Collector Cut-Off Current	$I_{CEO}$	$V_{CE}=32\text{V}$ , $V_{BE}=0$			100	$\mu\text{A}$
Emitter Cut-Off Current	$I_{EBO}$	$V_{EB}=5\text{V}$ , $I_C=0$			1	mA
DC Current Gain (Note 1)	$h_{FE}$	$V_{CE}=5\text{V}$ , $I_C=10\text{mA}$	40	130		
		$V_{CE}=1\text{V}$ , $I_C=500\text{mA}$	85	140		
		$V_{CE}=1\text{V}$ , $I_C=2\text{A}$	50			
Collector-Emitter Saturation Voltage (Note 1)	$V_{CE(SAT)}$	$I_C=2\text{A}$ , $I_B=0.2\text{A}$		0.2	0.5	V
Base-Emitter ON Voltage (Note 1)	$V_{BE(ON)}$	$V_{CE}=1\text{V}$ , $I_C=2\text{A}$			1.1	V
Current Gain Bandwidth Product	$f_T$	$V_{CE}=1\text{V}$ , $I_C=250\text{mA}$	3			MHz

Note: Pulse Test:  $P_W=300\mu\text{s}$ , duty Cycle=1.5% Pulsed

UTC assumes no responsibility for equipment failures that result from using products at values that exceed, even momentarily, rated values (such as maximum ratings, operating condition ranges, or other parameters) listed in products specifications of any and all UTC products described or contained herein. UTC products are not designed for use in life support appliances, devices or systems where malfunction of these products can be reasonably expected to result in personal injury. Reproduction in whole or in part is prohibited without the prior written consent of the copyright owner. The information presented in this document does not form part of any quotation or contract, is believed to be accurate and reliable and may be changed without notice.